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Substitute for form 1449A/PTO		Complete if Known	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>		Application Number	10/642,305
		Filing Date	August 18, 2003
		First Named Inventor	Hongyong ZHANG et al.
		Art Unit	2811
		Examiner Name	Douglas W. Owens
		Attorney Docket Number	740756-2646
Sheet	1	of	1
<b>OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS</b>			
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume- issue number(s), publisher, city and/or country where published.	
/DWO/		LEE, M.K. et al. "Control of Silicon Dioxide Properties by RF Sputtering", <u>Journal of the Electrochemical Society</u> , Vol. 130, No. 3, (March 1983) pp. 658-659.	
/DWO/		Expert Report on the Invalidity of U.S. Patents 5,352,291, Zhang et al. No. 6,177,302B1, Yamazaki et al., and No. 6,566,175B2, Yamazaki et al., by S. Wagner, September 24, 2006	
Examiner Signature	/Douglas W Owens/		Date Considered 05/14/2007

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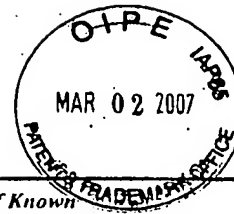
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/DWO/	1	Toppoly's Opposition Claim Construction Brief, May 30, 2006	
/DWO/	2	Declaration of Hector G. Gallegos in Support of Toppoly Optoelectronics Corp's. Opposition Claim Construction Brief, May 30, 2006	
/DWO/	3	Plaintiff and Counterclaim Defendant Semiconductor Energy Laboratory Co., Ltd.'s Memorandum of Points and Authorities in Opposition to Defendants' and Counterclaim Plaintiffs' Claim Construction Brief (signed on 05/26/2006), May 30, 2006	
/DWO/	4	Supplemental Declaration of Reginald J. Hill in Support of Semiconductor Energy Laboratory Co., Ltd.'s Claim Constructions (signed on 05/26/2006), May 30, 2006	
/DWO/	5	Toppoly Optoelectronics Corp.'s Supplemental Response to Semiconductor Energy Laboratory Co., Ltd.'s Interrogatory No. 4, June 21, 2006	
/DWO/	6	Order: Claim Construction Ruling, July 25, 2006	
/DWO/	7	Invalidity Report of Professor Gottlieb S. Oehrlein, September 22, 2006	
/DWO/	8	Expert on the Invalidity of U.S. Patents 5,352,291, Zhang et al. No. 6,177,302B1, Yamazaki et al., and No. 6,566,175B2, Yamazaki et al., by S. Wagner, September 24, 2006	

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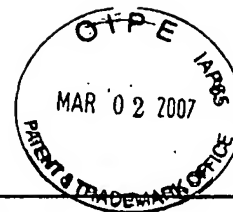
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/DWO/		ROHATGI A., et al. " <u>Chlorine Incorporation in HCl Oxides</u> ", <u>Journal of The Electrochemical Society</u> , Vol. 126, No. 1, (January 1979), pp. 143-148.	
/DWO/		ROHATGI A., et al. " <u>Mobile Sodium Ion Passivation in HCl Oxides</u> ," <u>Journal of the Electrochemical Society</u> , Vol. 126, No. 1, (January 1979), pp. 149-154.	
/DWO/		WILLIAMS, R. et al. " <u>Mobile Fluoride Ions in SiO<sub>2</sub></u> ", <u>Journal of Applied Physics</u> , Vol. 46, No. 2 (February 1975) pp. 695-698	
/DWO/		LEE, M.K. et al. " <u>Control of Silicon Dioxide Properties by RF Sputtering</u> ", <u>Journal of the Electrochemical Society</u> , Vol. 130, No. 3, (March 1983) pp. 685-859	
/DWO/		DASILVA, E.F. et al. " <u>Radiation Response of MOS Capacitors Containing Fluorinated Oxides</u> , <u>IEEE Transaction on Nuclear Science</u> , Vol. 34, No. 6, (December 1987) pp. 1190-1195.	
/DWO/		NISHIOKA, Y. et al. " <u>Dramatic Improvement of Hot-Electron-Induced Interface Degradation in MOS Structures Containing F or Cl in SiO<sub>2</sub></u> ", <u>IEEE Electron Device Letters</u> , Vol. 9, No. 1, (Jan. 1988), pp. 38-40.	
/DWO/		NISHIOKA, Y. et al. " <u>Dielectric Characteristics of Fluorinated Ultradry SiO<sub>2</sub></u> " <u>Applied Physics Letters</u> , Vol. 54, No. 12, (March 20, 1989), pp. 1127-1129	
/DWO/		NISHIOKA, Y. et al. " <u>Hot-Electron Hardened Si-Gate MOSFET Utilizing F-Implantation</u> ", <u>IEEE Electron Device Letters</u> , Vol. 10, No. 4, (April 1989), pp. 141-143.	
/DWO/		BRUNO, G. et al. " <u>Study of the NF<sub>3</sub> Plasma Cleaning of Reactors for Amorphous-Silicon Deposition</u> ", <u>Journal of Vacuum Science &amp; Technology A</u> , Vol. 12, No. 3, (1994), pp. 690-698	
/DWO/		JANSEN, F. et al. " <u>Contamination Effects in Glow-Discharge Deposition Systems</u> ", <u>Journal of Vacuum Science &amp; Technology A</u> , Vol. 6, No. 1, (1988), pp. 13-18	
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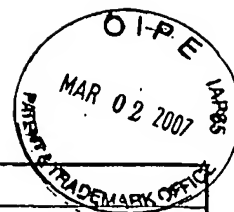
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/DWO/		KARULKAR, P.C. et al., "XPS AES Investigation of Cross Contamination in a Plasma Etcher", <u>Journal of Vacuum Science &amp; Technology B</u> , Vol. 3, No. 3, (1985), pp. 889-891	
/DWO/		Exhibit 7, Asserted Claim Chart - Sano Reference, JP 64-35959	
/DWO/		FRANCOIS-SAINT-CYR, et al. "Diffusion of 18 elements implanted into thermally grown SiO <sub>2</sub> ", <u>Journal of Applied Physics</u> , Vol. 94, No. 12, (December 15, 2003), pp. 7433-7439	
/DWO/		DATAR, S.A. et al. "AMS Studies of the Diffusion of Chlorine in Silicon-Wafers" <u>Nuclear Instruments &amp; Methods in Physics Research- B 99 - Beam Interactions with Materials and Atoms</u> , (1995), pp. 549-552	
/DWO/		TSENG, H.H. et al. "Fluorine Diffusion on a Polysilicon Grain-Boundary Network in Relation to Boron Penetration from P+ Gates", <u>IEEE Electron Device Letters</u> , Vol. 13, No. 1, (January 1992), pp. 14-16	
/DWO/		TROXELL, JOHN R. et al. "Polycrystalline Silicon Thin-Film Transistors on a Novel 800°C Glass Substrate", <u>IEEE Electron Device Letters</u> , Vol. 7, No. 11, (November 1986), pp. 597-599	
/DWO/		ERMOLIEFF, A. et al. "XPS Studies of Contamination of Reactor and Silicon Surfaces Caused by Reactive Ion Etching", <u>Semiconductor Science and Technology</u> , Vol. 6, (1991), pp. 290-295	
/DWO/		ERMOLIEFF, A. et al. "X-Ray Photoelectron-Spectroscopy Studies of Contamination and Cleaning of Surfaces Exposed to a Fluorocarbon Plasma", <u>Journal of Vacuum Science &amp; Technology A</u> , Vol. 9, No. 6, (November/December 1991), pp. 2900-2906	

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/DWO/		IQBAL, Z. et al. "Raman scattering from hydrogenated microcrystalline and amorphous silicon", J. Phys. C. Solid State Phys., Vol. 15 (1982) pp. 377-392	
/DWO/		JENG, S.P. et al. "Anomalous Diffusion of Fluorine in Silicon", <u>Applied Physics Letters</u> , Vol. 61, No. 11, (September 14, 1992), pp. 1310-1312	
/DWO/		YOUNG, N.D. et al. "Mobile ion instabilities in polycrystalline silicon thin film transistors" <u>Applied Surface Science</u> , Vol. 39, (1989), pp. 364-367	
/DWO/		SAMESHIMA et al. "XeCl Excimer Annealing Used to Fabricate Poly-Si TFT's", <u>IEEE Electronic Device Letters</u> , Vol. 7, No. 5, (May 1986), pp. 276-278	
/DWO/		KAKKAD et al. "Crystallized Si films by low-temperature rapid thermal annealing of amorphous silicon", J. Applied Physics, Vol. 65, No. 5, (March 1, 1989), pp. 2069-2072	
/DWO/		PINARBASI, M. et al., "Hydrogenated Amorphous Silicon Films Deposited by DC Planar Magnetron Reactive Sputtering", <u>Superlattices and Microstructure</u> , Vol. 3, No. 4, (1987) pp. 331-340	
/DWO/		MADAN, A. et al. "Characterization of Schottky Barriers", <u>The Physics and Applications of Amorphous Semiconductors</u> , Academic Press, pp. 193-197	
/DWO/		MADAN et al. "Use of PECVD System in Thin Film Technology", Workshop on Industrial Plasma Applications, pp. 1-10	
/DWO/		MALEY, N. et al. "Infrared absorption and thermal evolution study and hydrogen bonding in a-SiH", <u>Journal of Vacuum Science &amp; Technology</u> , Vol. 7, No. 3, (May/June 1989), pp. 1267-1270	

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/DWO/		US-4,007,294	02/08/1977	Woods et al.	
/DWO/		US-4,485,146	11/27/1984	Mizuhashi et al.	
/DWO/		US-4,657,616	04/14/1987	Benzing et al.	
/DWO/		US-4,786,352	11/22/1988	Benzing	
/DWO/		US-4,851,363	07/25/1989	Troxell et al.	
/DWO/		US-7,097,716 B2	08/29/2006	Barnes et al.	
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/DWO/		JP	01-268064	10/25/1989			FULL

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